

Transistors with Built-in Resistor DRC5124E0L

DRC5124E0L Silicon NPN epitaxial planar type

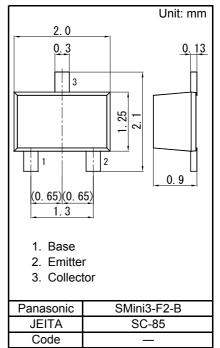
For digital circuits Complementary to DRA5124E DRC2124E in SMini3 type package

Features

- · Low collector-emitter saturation voltage Vce(sat)
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)
- Marking Symbol: NE

Packaging

Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)



Internal Connection						
$B \circ R_1 \circ C$ $R_2 \circ E$						
Resistance	R1	22	kΩ			
value	R2	22	kΩ			

■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	VCBO	50	V
Collector-emitter voltage (Base open)	VCEO	50	V
Collector current	IC	100	mA
Total power dissipation	PT	150	mW
Junction temperature	Tj	150	°C
Operating ambient temperature	Topr	-40 to +85	°C
Storage temperature	Tstg	-55 to +150	С°

Electrical Characteristics	Ta = 25 °C ± 3 °C
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Electrical offaracteristics Ta = 20 0		Conditions	Mim	T	Max	1 1
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	VCBO	IC = 10 µA, IE = 0	50			V
Collector-emitter voltage (Base open)	VCEO	IC = 2 mA, IB = 0	50			V
Collector-base cutoff current (Emitter open)	ICBO	VCB = 50 V, IE = 0			0.1	μA
Collector-emitter cutoff current (Base open)	ICEO	VCE = 50 V, IB = 0			0.5	μA
Emitter-base cutoff current (Collector open)	IEBO	VEB = 6 V, IC = 0			0.2	mA
Forward current transfer ratio	hFE	VCE = 10 V, IC = 5 mA	60			-
Collector-emitter saturation voltage	VCE(sat)	IC = 10 mA, IB = 0.5 mA			0.25	V
Input voltage	Vi(on)	VCE = 0.2 V, IC = 5 mA	2.6			V
	Vi(off)	VCE = 5 V, IC = 100 µA			0.8	V
Input resistance	R1		-30%	22	+30%	kΩ
Resistance ratio	R1/R2		0.8	1.0	1.2	-

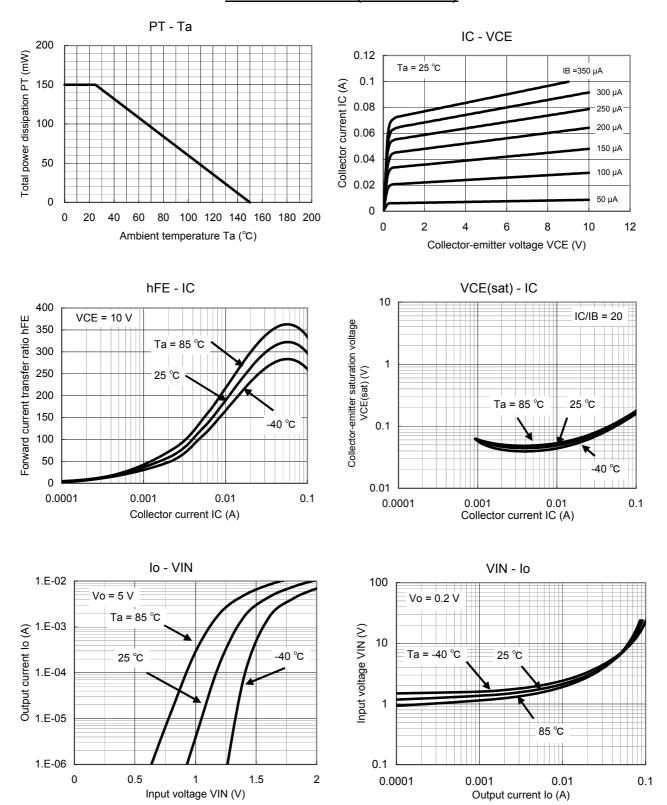
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.



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Technical Data (reference)

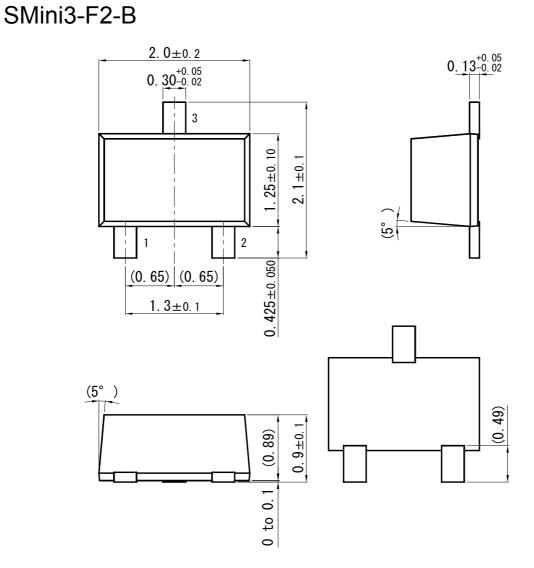


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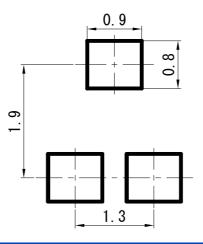
Established : 2009-10-15 Revised : 2014-03-18



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Land Pattern (Reference) (Unit: mm)



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